

IN THE ABSTRACT

Amend the Abstract as follows:

A magnetic recording medium which comprises a substrate, an orientation control layer formed directly thereon, and a Co alloy magnetic layer formed thereon directly or indirectly with a Cr underlayer or Cr alloy underlayer interposed between them, said the orientation control layer having the an L10 crystal structure, L21 crystal structure, fcc crystal structure, or B2 (CsC1) crystal structure containing B, Owing owing to this construction, the magnetic recording medium has a high coercive force and a low noise level and is only slightly vulnerable to thermal fluctuation. A magnetic storage device having a magnetic recording medium, a driver to turn said magnetic recording medium in the recording direction, a magnetic head ~~consisting of~~ including a recording element and a read-back element, a means to move said the magnetic head relative to said the magnetic recording medium, and a record-read signal processing means to perform waveform processing on input signals to and output signals from said the magnetic head, wherein said uses this magnetic recording medium ~~is the one mentioned above~~ and the has a magnetoresistive effect read-back element ~~of~~ said in its magnetic head is that of magnetoresistive effect ~~type~~. This magnetic storage device has a recording density in excess of 3 Gbit/in².